

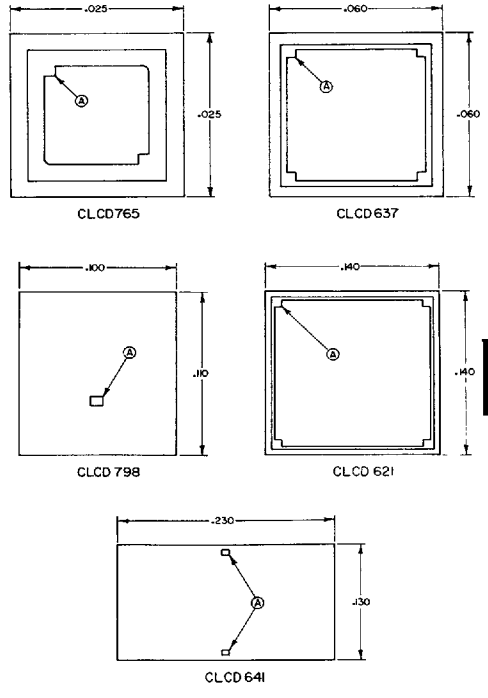
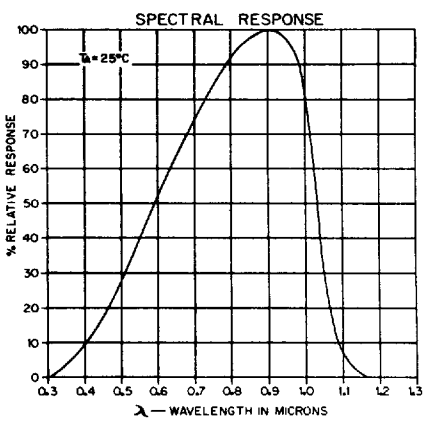
# Photovoltaic Diode Chips

Clairex offers a broad range of custom and stock photodiode designs. Chips may be selected for special electrical requirements, i.e., light sensitivity, break-down voltage, dark current, etc. All chips have gold backing suitable for either eutectic or conductive

epoxy ohmic die attachment. Aluminum pads accept either thermocompression ball or ultrasonic wedge wire bonding. Packaging of chips may be in glass vials, "waffle" carriers or other suitable means.

Symbol	Characteristics	Test Conditions	CLCD765	CLCD637	CLCD798	CLCD621	CLCD641	Unit
LXW	Active Area		.015 x .015	.051 x .051	.082 x .090	.125 x .125	.124 x .218	inches
I <sub>sc</sub>	Short Circuit Current (1) Minimum	H = 5mw/cm <sup>2</sup> (1)	1	8	30	50	100	μA
I <sub>d</sub>	Dark Current Maximum	H = 0, V = -100mV	10	10	25	25	25	nA
C <sub>j</sub>	Junction Capacitance	0 bias with f = 1MHZ	7	35	85	200	280	pf
t <sub>r</sub> , t <sub>f</sub>	Rise or Fall Time — typical	V = 0, R <sub>L</sub> = 1KΩ (2)	4	5	8	10	15	μsec

Note 1: The light source is a frosted tungsten incandescent lamp at 2854°K.  
 Note 2: The light source is a gallium arsenide LED pulsed with a rise and fall time of < 0.3 μ sec.  
 All characteristics are specified at 25°C.



**A = ANODE**  
**BACK OF CHIP IS CATHODE**  
**ALL DEVICES ARE P ON N CONSTRUCTION**

11